

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

MAEDA et al

Serial No.:

Filed: March 15, 2001

For: FILM-FORMING SURFACE REFORMING METHOD AND  
SEMICONDUCTOR DEVICE MANUFACTURING METHOD

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claims 12 as follows:

12. (Amended) A semiconductor device manufacturing method according to claim 6, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

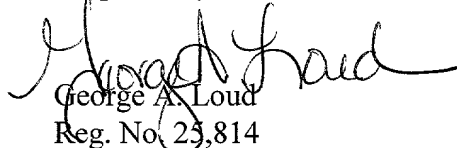
Please add the following new claims:

--13. A semiconductor device manufacturing method according to claim 7, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

14. A semiconductor device manufacturing method according to claim 8, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

15. A semiconductor device manufacturing method according to claim 11, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.--

Respectfully submitted,

  
George A. Loud  
Reg. No. 23,814

Dated: March 15, 2001

LORUSSO & LOUD  
3137 Mount Vernon Avenue  
Alexandria, VA 22305  
(703) 739-9393

12. (Amended) A semiconductor device manufacturing method according to claim 6 [any one of claims 6, 7, 8, and 11], wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.